

SOT-523 Plastic-Encapsulated Diode

DAN222

SWITCHING DIODE

FEATURES:

Power dissipation

P_D : 150 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

I_F : 100 mA

Collector-base voltage

V_R : 80 V

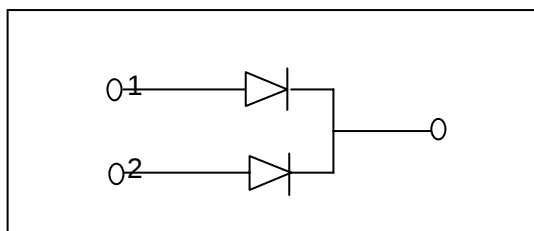
Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

SOT-523



CIRCUIT:



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MARKING: N

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu\text{A}$	80		V
Reverse voltage leakage current	I_R	$V_R = 70\text{V}$		0.1	μA
Forward voltage	V_F	$I_F = 100\text{mA}$		1.2	V
Diode capacitance	C_D	$V_R = 6\text{V}, f = 1\text{MHz}$		3.5	pF
Reverse recovery time	t_{rr}	$V_R = 6\text{V}, I_F = 5\text{mA}$		4	ns